	*	Type	L #	Hits	S arch T xt	DBs	Time Stamp
						USPAT	
						;	
				A		US-PG PUB;	
	7	DDG	7.110	60005	TFT or "thin film	•	2004/05/11
	1	BRS	ГПТЭ	60885	transistor"	JPO;	19:52
i	•					DERWE	*
						NT;	
						IBM_T DB	
1						USPAT	
		*	,			USPAI	
		4				, US-PG	
		* *				PUB;	
	2 -	BRS	L120	195609			2004/05/11
.				β .			19:52
1			,			DERWE NT;	
		* "	Ŋ.			IBM T	
L						DB	4 1
. [17			USPAT	
1	•					;	* '
				17	(nol-mhomlo	US-PG	
				** <u>**</u>	(polyphenylene near2 polyimide) or	PUB;	2004/05/11
	3	BRS	L121	1726			2004/05/11 19:52
				*		DERWE	10.02
		,	•			NT;	
		-				IBM_T	
ŀ						DB	
	×					USPAT	
	1.		1.7			; US-PG	
						PUB;	
1	4	BRS	L125		upilex-50ss or "URE	EPO;	2004/05/11
	. *				America"		19:52
	.					DERWE	
		1.7			•	NT; IBM T	
						DB	
Γ						USPAT	·····
				• 00	* "	,	
1	* :				#	US-PG	
				·. [PUB;	2004/05/33
5	5	IS&R	L127	994			2004/05/11 19:52
ĺ		.		•		DERWE	17.04
1						NT;	
						IBM_T	
L				<u></u>		DB	

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10 BRS L123 28		Тур	L #	Hits	S arch T xt	DBs	Tim Stamp
Sar L129 304 (438/155).CCLS. PUB; EPO; JPO; DERWE NT; IBM_T DB USPAT (substrate base wafer bulk) with (polyphenylene near3 polyimide\$2) USPAT (substrate base wafer bulk) Wispar DB USPAT (substrate base wafer bulk) Wispar DB USPAT (substrate base wafer bulk) Wispar DB USPAT (substrate base wafer bulk) PUB; EPO; JPO; DERWE NT; IBM_T DB USPAT (substrate or wafer) near4 (substrate or wafer) near5 (substrat						USPAT	-
Series	-)	, .				;	
SER							
10 BRS L123 28 Polymide Polymenylene		5			*	•	
19:52	6	IS&R	L129	304	(438/155).CCLS.		2004/05/11
NT; IBM T DB							19:52
TBM_T DB						-	` .
BRS		4.4					
Second S							
The content of the	110					<u> </u>	
(substrate base wafer bulk) with (polyphenylene near3 polyimide\$2) (substrate base wafer bulk) polyimide\$2) (substrate base wafer bulk) polyimide\$2 (substrate or wafer) polyimide\$2 ((substrate or wafer) near4 US-PG ((polyphenylene near2 polyimide)) polyimide) or ((poly-phenylene near2 polyimide)) polyimide) or ((polyphenylene near4 US-PG polyimide)) polyimide) ((substrate or wafer) near4 US-PG polyimide) ((polyphenylene near2 polyimide)) polyimide) ((substrate or wafer) near4 (polyphenylene near2 polyimide) polyimide) ((substrate or wafer) near4 (polyphenylene near2 polyimide) polyimide) ((substrate or wafer) near4 polyphenylene near2 polyimide) ((substrate or wafer) near4 polyphenylene near2 polyphenylene nea	7					USPAT	
(substrate base wafer bulk) with (polyphenylene near3 polyimide\$2) (substrate base wafer bulk) polyimide\$2) (substrate base wafer bulk) polyimide\$2 (substrate or wafer) polyimide\$2 ((substrate or wafer) near4 US-PG ((polyphenylene near2 polyimide)) polyimide) or ((poly-phenylene near2 polyimide)) polyimide) or ((polyphenylene near4 US-PG polyimide)) polyimide) ((substrate or wafer) near4 US-PG polyimide) ((polyphenylene near2 polyimide)) polyimide) ((substrate or wafer) near4 (polyphenylene near2 polyimide) polyimide) ((substrate or wafer) near4 (polyphenylene near2 polyimide) polyimide) ((substrate or wafer) near4 polyphenylene near2 polyimide) ((substrate or wafer) near4 polyphenylene near2 polyphenylene nea				. 1		iic DC	
Series							
BRS L122 Section S	_						2004/05/11
BRS L133 875 (substrate base wafer bulk) (substrate base wafer bulk) with (polyphenylene and polyimide\$2) (substrate or wafer) near4 (substrate or wafer) near4 (substrate or wafer) near4 (substrate or wafer) near4 (substrate) near2 polyimide) or (poly-phenylene near2 polyimide)) and (TFT or "thin film transistor") DERWE "T; IBM T DB (substrate or wafer) near4 (substrate	7	BRS	L131	315			
8 BRS L133 875 (substrate base wafer bulk) (US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB ((substrate or wafer) near4 US-PG ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or "thin film transistor") ((substrate or wafer) near4 (US-PG PUB; EPO; 19:53) ((substrate or wafer) near4 ((polyphenylene near2 polyimide))	1				polyimide\$2)		17.32
8 BRS L133 875 (substrate base wafer bulk) Wis-PG PUB; EPO; JPO; DERWE NT; IBM_T DB 9 BRS L122 2 ((substrate or wafer) near4 US-PG ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) and (TFT or "thin film transistor") DERWE NT; IBM_T DB 10 BRS L123 28 (substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) and (TFT or "thin film transistor") DERWE NT; IBM_T DB (substrate or wafer) near4 ((polyphenylene near2 polyimide)) DERWE NT; IBM_T DB (substrate or wafer) near4 ((polyphenylene near2 polyimide)) DERWE NT; IBM_T DB (substrate or wafer) near4 (polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide) DERWE NT; IBM_T DB; IBM_T DB	۰						·
Series (substrate base wafer bulk) (substrate base wafer bulk) (with (polyphenylene and polyimide\$2) (substrate or wafer) near4 (substrate or wafer) near4 (substrate or wafer) near4 (substrate or wafer) near4 (substrate) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide)) and (TFT or substrate or wafer) near4 (substrate or			,				* /
8 BRS L133 875 (substrate base wafer bulk) with (polyphenylene and polyimide\$2) 9 BRS L122 2 ((substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or "thin film transistor") 10 BRS L123 28 (substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) (substrate or wafer) near4 (substrate or wafer) near4 ((polyphenylene near2 polyimide)) (substrate or wafer) near4 (substrate or wafer) near4 (polyphenylene near2 polyimide)) (substrate or wafer) near4 (substrate or wafer) near4 (polyphenylene near2 polyimide)) (substrate or wafer) near4 (substrate or wafer) near4 (polyphenylene near2 polyimide)) (substrate or wafer) near4 (substrate or wafer) near4 (polyphenylene near2 polyimide))	1			· 1	*	_	
8 BRS L133 875 (substrate base wafer bulk) with (polyphenylene and polyimide\$2) 9 BRS L122 2 ((substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or "thin film transistor") 10 BRS L123 28 (substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) (substrate or wafer) near4 (substrate or wafer) near4 ((polyphenylene near2 polyimide)) (substrate or wafer) near4 (substrate or wafer) near4 (polyphenylene near2 polyimide)) (substrate or wafer) near4 (substrate or wafer) near4 (polyphenylene near2 polyimide)) (substrate or wafer) near4 (substrate or wafer) near4 (polyphenylene near2 polyimide)) (substrate or wafer) near4 (substrate or wafer) near4 (polyphenylene near2 polyimide))				•••••		USPAT	
Series (substrate base wafer bulk) with (polyphenylene and polyimide\$2) 2004/05/1 19:53 2004/05/1 19:53 2004/05/1 19:53 2004/05/1 2004	, .					;	
8 BRS L133 875 with (polyphenylene and polyimide\$2) EPO; JPO; DERWE NT; IBM_T DB ((substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or "thin film transistor") EPO; JPO; DERWE NT; IBM_T DB (substrate or wafer) near4 ((polyphenylene near2 polyimide)) and (TFT or "thin film transistor") (substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide)) (substrate or wafer) near4 (JPO; DERWE NT; DPO; DERWE NT; DPO; DERWE NT;		,	*	0	0.	US-PG	()
BRS L133 875 with (polyphenylene and polyimide\$2) 19:53 19					(substrate base wafer bulk)	PUB;	
polyimide\$2) polyimide\$2 polyimide\$2) polyimide\$2 polyimide\$2	l ₈	BRS	T.1 2 2	875		EPO;	2004/05/11
BRS L122 2 ((substrate or wafer) near4 ((substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or "thin film transistor") DERWE NT; IBM_T DB ((substrate or wafer) near4 ((polyphenylene near2 polyimide)) and (IFT or USPAT ; IBM_T DB ((substrate or wafer) near4 ((polyphenylene near2 polyimide))		JICD ,	1133	075	polyimide\$2)		19:53
Substrate or wafer) near4 Suspar		-					
9 BRS L122 2 ((substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or "thin film transistor") (substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide)) [Substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) [Substrate or wafer) near4 (polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))			. *1	*	*		
9 BRS L122 2 ((substrate or wafer) near4 (US-PG (polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or polyimide))) and (TFT or DERWE "thin film transistor") 10 BRS L123 28 (substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide)) (substrate or wafer) near4 (US-PG PUB; EPO; JS-PG PUB; EPO; JPO; DERWE NT;		*	= X =	,			
((substrate or wafer) near4 US-PG PUB; EPO; 2004/05/1 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or "thin film transistor") ((substrate or wafer) near4 (substrate or wafer) near4 ((polyphenylene near2 polyimide)) ((substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) (substrate or wafer) near4 (polyphenylene near2 polyimide)	,			, P			
9 BRS L122 2 ((polyphenylene near2 polyimide) or (poly-phenylene near2 JPO; polyimide))) and (TFT or polyimide))) and (TFT or DERWE "thin film transistor") (substrate or wafer) near4 (polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide)) (substrate or wafer) near4 (ISPPG PUB; EPO; JPO; DERWE NT; DERWE NT;				,		USPAT	
9 BRS L122 2 ((polyphenylene near2 polyimide) or (poly-phenylene near2 JPO; polyimide))) and (TFT or polyimide))) and (TFT or DERWE "thin film transistor") (substrate or wafer) near4 (polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide)) (substrate or wafer) near4 (ISPPG PUB; EPO; JPO; DERWE NT; DERWE NT;			• .		((a)batrata an (afan)	;	
9 BRS L122 2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or DERWE NT; IBM_T DB (substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide)) (substrate or wafer) near4 (190 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide)) (substrate or wafer) near4 (190 polyimide) or (poly-phenylene near2 polyimide) or (poly-phenylene near2 polyimide))		•					
(substrate or wafer) near4 (polyphenylene near2 polyimide) or (polyphenylene near2 polyimide)) (polyphenylene near2 polyimide) or (polyphenylene near2 polyimide) or (polyphenylene near2 polyimide))		Đ	* 1	•			2004/05/11
polyimide))) and (TFT or "thin film transistor") "thin film transistor") "IBM_T DB USPAT ; US-PG PUB; EPO; JPO; JPO; JPO; DERWE NT;	9	BRS	L122	2		17.4	
"thin film transistor") NT; IBM_T DB (substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) US-PG PUB; EPO; JPO; JPO; DERWE NT;	1				polvimide))) and (TET or		19:53
IBM_T DB USPAT ; US-PG PUB; EPO; polyimide) or (poly-phenylene near2 polyimide)) USPAT ; US-PG PUB; EPO; JPO; DERWE NT;							
DB							
(substrate or wafer) near4 (polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) USPAT; US-PG PUB; EPO; JPO; DERWE NT;	1					· —	
(substrate or wafer) near4 (polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) 10 BRS L123 28 (substrate or wafer) near4 (US-PG PUB; EPO; JPO; JPO; DERWE NT;			***************************************				
(substrate or wafer) near4 (puB; EPO; 2004/05/1 polyimide) or (poly-phenylene near2 polyimide)) (substrate or wafer) near4 PUB; EPO; JPO; DERWE NT;	'						
10 BRS L123 28 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)) PUB; EPO; 2004/05/1 JPO; DERWE NT;] .				()		97 - 1 7
BRS L123 28 polyimide) or (poly-phenylene near2 polyimide)) [PO; DERWE NT; 2004/05/1 polyimide)]			. •		(Substrace or water) Hear4		·
polyimide) of (poly-phenylene near2 polyimide)) JPO; DERWE NT;		DDC	T100	20			2004/05/11
polyimide)) DERWE NT;	1_0	מאם	TT 7.3	∠8 ·	borlinge, or		
NT;							-
		- "e" -	~)			
i						IBM_T	
DB D						DB _	

		Тур	L #	Hits	Search Text	DBs	Time Stamp
			-			USPAT	
,						<i>;</i>	
ĺ					((polyphenylene near2	US-PG	
	· _		*		polyimide) or	PUB; EPO;	2004/05/11
	11	BRS	L124	18	(poly-phenylene near2	JPO;	19:53
	•			*	polyimide)) and (TFT or "thin film transistor")	DERWE	
ļ					chin liim clansistor)	NT;	
l						IBM_T	
ŀ						DB	
1	•					USPAT	
						; US-PG	
1				* * * * * * * * * * * * * * * * * * * *	(upilex-s or upilex-vt or	PUB;	
	12	DD-C	T 106		upilex-50ss or "UBE	EPO;	2004/05/11
1	12 .	BRS	L126	9	America") and (TFT or "thin	JPO;	19:53
1						DERWE	
	٠. *	:				NT;	- , , , , , , , , , , , , , , , , , , ,
						IBM_T	
F	·				,	DB	
ļ						USPAT	
	,		- 1			;	, , ,
	•		÷		((438/149).CCLS.) and	US-PG PUB;	
				_	((polyphenylene near2	EPO;	2004/05/11
ŀ	13	BRS	L128	2	polyimide) or	JPO;	
ŀ					<pre>(poly-phenylene near2 polyimide))</pre>	DERWE	7,00
		*	.00		pory milde//	NT;	
	,			, 7,		IBM_T	
×	· .	*	***************************************			DB	* * *
l	-	* v				USPAT	* * *
ļ						;	
				*	//=>o/ Too/ .ccmp./ aird	US-PG PUB;	
1					((borabilenatelle lieurs	EPO;	2004/05/11
	L4	BRS	L130	1	poryrmide, or	JPO;	19:53
			*		<pre>(poly-phenylene near2 polyimide))</pre>	DERWE	
					poryrmide))	NT;	
ı		÷	,	'		IBM_T	
L	- 1					DB	
l		1				USPAT	
	,]			• ', '		;	
		=			(Substiate base water	US-PG	
					park, with (borybuenyrene	PUB; EPO;	2004/05/11
$ ^1$	L5	BRS	L132	223	nears poryrillaesz// and	JPO;	19:53
				. ' 1	184472000410	DERWE	
ĺ	. *	·		;·,	@IIAU<20000416/	NT;	
		< ,				IBM_T	
L						DB .	

	Туре	L #	Hits	Search T xt	DBs	Tim Stamp
16	BRS	L134	597	((substrate base wafer bulk) with (polyphenylene and polyimide\$2)) and (@ad<20000418 @rlad<20000418)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/05/11 19:53
17	BRS	L135	152	bulk) with (polyphenylene and polyimide\$2)) and (@ad<20000418 @rlad<20000418)) and (chip semiconductor)	JPO:	2004/05/11 19:53

	Тур	L #	Hits	Search T xt	DBs	Tim Stamp
1	BRS	L1	60885	TFT or "thin film	USPAT; US-PGP UB; EPO; JPO;	2004/05/11
				transistor"	DERWEN T; IBM_TD B	0)
2	BRS	L2	195609 9	substrate or wafer	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:45
3	BRS	L4	1726	(polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:45
4	BRS	L6	2	5 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:46
5	BRS	L5	28	2 near4 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 10:49

	Type	L #:	Hits	Search Text	DBs	Time Stamp
6	BRS	L7	18	4 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD	2004/05/11 10:55
7	BRS	L8		upilex-s or upilex-vt or upilex-50ss or "UBE America"	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD	2004/05/11 10:55
8	BRS	L9	9	8 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 11:00
9	IS&R	L10	994	(438/149).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 11:00
10	BRS	L11	2	10 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/11 11:03

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:	Туре	L #	Hits	S arch Text	DBs	Time Stamp
			·		USPAT; US-PGP	
	. ,	*			UB; EPO;	
11	IS&R	L12	304	(438/155).CCLS.	JPO; DERWEN	2004/05/11 11:03
					T; IBM_TD B	
			*		USPAT; US-PGP UB; EPO;	
12	BRS	L15	1	12 and 4	JPO; DERWEN	2004/05/11 11:04
, ,			ž		T; IBM_TD B	

		Туре	L #	Hits	Search T xt	DBs	Time Stamp
Ì						USPAT	
1	•					;	
1		, .				US-PG	,
Ì			,			PUB;	
١	1	BRS	L1	60969	TFT or "thin film	•	2004/05/13
1					transistor"		12:57
۱						DERWE	
١					,	NT;	,
	•					IBM_T	•
-		·····				DB	
					4	USPAT	
	;					;	
ľ						US-PG	
		,		1,05252		PUB;	2004/05/22
	2	BRS	L2	195737 3	substrate or wafer		2004/05/13
		,		J		JPO; DERWE	12:57
	8					DERWE NT;	
١	Ì	*				IBM T	
ı						DB	
ŀ						USPAT	
						;	
١						, US-PG	
١					(polyphenylene near2	PUB;	_
.	,		- 0		polyimide) or		2004/05/13
1	3	BRS	L3	1730	(poly-phenylene near2	JPO;	12:57
l			· 1,			DERWE	
1		, t. 15	4			NT;	
	1		-			IBM_T	
						DB	
ı	*					USPAT	
			. •			;	**
ŀ						US-PG	
		~		1	upilex-s or upilex-vt or	PUB;	
	4	BRS	L4	730	upilex-50ss or "UBE	EPO;	2004/05/13
ı		•	*	ì	America"	JPO;	12:57
1	٠			`		DERWE	*
١						NT; IBM T	
1	1-					DB TEM_1	-
╌┠						*******************	
			÷			USPAT	
	•••					; US-PG	
	-		*			PUB;	
	_	TOCE	T. E.	005	(420/740) =====	EPO;	2004/05/13
	5	IS&R	L5	996	(438/149).CCLS.	JPO;	12:57
					*	DERWE	
	٠		-	-		NT;	
	.		0		· · · · · · · · · · · · · · · · · · ·	IBM_T	
				,		ĎB _	•

		Type	L #	Hits	Search T xt	DBs	Time Stamp
	•	BRS	L6	316	(substrate base wafer bulk) with (polyphenylene near3	USPAT; US-PG PUB; EPO;	2004/05/13
					polyimide\$2)	JPO; DERWE NT; IBM_T DB	12:57
7,	7	BRS	L 7	877	(substrate base wafer bulk) with (polyphenylene and polyimide\$2)	; US-PG PUB; EPO; JPO; DERWE NT; IBM T	2004/05/13 12:57
8		IS&R	L17	304		DERWE NT; IBM_T	2004/05/13 12:58
9		BRS	L8	۷۰	((substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))) and (TFT or "thin film transistor")	PUB; EPO;	2004/05/13 12:58
1(0	BRS	L 9	28	(substrate or wafer) near4 ((polyphenylene near2 polyimide) or (poly-phenylene near2 polyimide))		2004/05/13 12:58

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ŀ	. • .	Туре	L #	Hits	Search Text	DBs	Time Stamp
						USPAT	
*				*	((polyphenylene near2	US-PG	*
					polyimide) or	PUB;	2004/05/72
	.1	BRS	L10	18	(poly-phenylene near2	EPO; JPO;	2004/05/13 12:58
				13.3	<pre>polyimide)) and (TFT or "thin film transistor")</pre>	DERWE	12.50
			,		January Clausiston	NT;	
			1			IBM_T DB	
	: ,					USPAT	
						;	
1					(),mila	US-PG	
	_		*		(upilex-s or upilex-vt or upilex-50ss or "UBE	PUB;	2004/05/12
	2	BRS	L11	9	America") and (TFT or "thir	EPO;	2004/05/13 12:58
1.				r aj	film transistor")	DERWE	12.30
		1				NT;	
1						IBM_T DB	
						USPAT	
	• *			1.02		;	
				<i>*</i>	((438/149).CCLS.) and	US-PG	
					((polyphenylene near2	PUB;	2004/05/12
1.	ک .	BRS	L12	2	polyimide) or (poly-phenylene near2	EPO; JPO;	2004/05/13 12:58
				,	polyimide))	DERWE	
			."			NT;	
						IBM_T DB	
	. W			7		USPAT	
	٠.			*		;	-
1		6 ×	-		((substrate base wafer	US-PG	
14	,	DDC 1	r 1 2	202	bulk) with (polyphenylene	PUB; EPO;	2004/05/13
1 -	±	BRS]	L13	223	near3 polyimide\$2)) and (@ad<20000418		12:58
					@rlad<20000418)	DERWE	
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Thin-film transistors on plastic and glass substrates silicon deposited by microwave plasma ECR-CVD

Lihong Teng Anderson, W.A.

Dept. of Electr. Eng., State Univ. of New York, Buffalo, NY, USA This paper appears in: Electron Device Letters, IEEE

Publication Date: June 2003 On page(s): 399 - 401 Volume: 24 , Issue: 6 ISSN: 0741-3106

Inspec Accession Number: 7701417

Abstract:

Thin-film **transistors** (TFTs) were fabricated on **polyimide** and glass substra temperatures using microwave ECR-CVD deposited amorphous and nanocryst as active layers. The amorphous Si TFT fabricated at 200 /spl deg/C on the perfoil had a saturation region field effect mobility of 4.5 cm/sup 2//V-s, a linear mobility of 5.1 cm/sup 2//V-s, a threshold voltage of 3.7 V, a subthreshold sv V/decade, and an ON/OFF current ratio of 7.9 /spl times/ 10/sup 6/. This larg and high ON/OFF current ratio were attributed to the high-quality channel ma less dangling bond defect states. Nanocrystalline Si TFTs fabricated on glass s at 400 /spl deg/C showed a saturation region mobility of 14.1 cm/sup 2//V-s, region mobility of 15.3 cm/sup 2//V-s, a threshold voltage of 3.6 V, and an O current ratio of 6.7 /spl times/ 10/sup 6/. TFT performance was mostly indeposubstrate type when fabrication conditions were the same.

Index Terms:

amorphous semiconductors carrier mobility dangling bonds elemental semiconductor hydrogen nanostructured materials plasma CVD silicon thin film transistors 200 (V 400 C ON/OFF current ratio Si:H-SiO/sub 2/ TFTs amorphous Si TFT amorphous dangling bond defect states glass substrates high-quality channel materials hydroger linear region mobility low temperature fabrication microwave plasma ECR-CVD nano TFTs nanocrystalline silicon polyimide foil polyimide substrates saturation region mobility silicon deposition subthreshold swing thin-film transistors threshold voltage

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